

**Amendments to the Claims**

Claims 1-192 are cancelled.

193. (Currently amended) A means for forming a Cu barrier layer by sputter-depositing a film from a target comprising Ti and one or more alloying elements selected from the group consisting of Be, B, Al, Si, Ca, Sc, V, Cr, Mn, Fe, Sr, Y, Zr, Cs, Ba, La, Hf, Ta, Ce, Pr, Nd, Sm, Gd, Dy, Ho and Er.

194. (Previously presented) The means of claim 193 wherein the one or more alloying elements comprise Zr.

195. (Previously presented) The means of claim 193 wherein the one or more alloying elements comprise V.

196. (Previously presented) The means of claim 193 wherein the one or more alloying elements comprise Cr.

197. (Previously presented) The means of claim 193 wherein the one or more alloying elements comprise Mn.

198. (Previously presented) The means of claim 193 wherein the one or more alloying elements comprise Fe.

199. (Previously presented) The means of claim 193 wherein the one or more alloying elements comprise Al.

200. (Currently amended) A method of inhibiting copper diffusion into a substrate, comprising:

forming a first layer comprising Ti and one or more alloying elements over the substrate, the one or more alloying elements including having at least one of Be, B, Al, Si, Ca, Sc, V, Cr, Mn, Fe, Sr, Y, Zr, Cs, Ba, La, Hf, Ce, Pr, Nd, Sm, Gd, Dy, Ho and Er; ~~of: (1) a standard electrode potential of less than about -1.0V; (2) a melting temperature of at least about 2400°C; and (3) at least an 8 percent difference in atomic radii relative to titanium; and~~

forming a copper-containing layer over the first layer, the first layer inhibiting copper diffusion from the copper-containing layer into the substrate.

201. (Previously presented) The method of claim 200 wherein the copper-containing layer is a copper-based layer.

202. (Currently amended) The method of claim 200 wherein at least one of the ~~one or more~~ alloying elements in the sputtering component is an element ~~are elements~~ having the standard electrode potential of less than about -1.0V selected from the group consisting of Be, B, Al, Si, Ca, Sc, V, Cr, Mn, Fe, Sr, Y, Zr, Cs, Ba, La, Hf, Ta, Ce, Pr, Nd, Sm, Gd, Dy, Ho and Er.

203. (Currently amended) The method of claim 200 wherein at least one of the ~~one or more~~ alloying elements in the sputtering component is an element ~~are elements~~ having at least an 8 percent difference in atomic radii relative to titanium, selected from the group consisting of Al, Ca, Mn, Fe, Co, Ni, Y, Zr, Hf, Be, B, C, Si, P, S, Cs, Ba, La, Ce, Pr, Nd, Sm, Gd, Dy, Ho, Er and Yb.

204. (Currently amended) The method of claim 200 wherein at least one of the ~~one or more~~ alloying elements in the sputtering component is an element ~~are elements~~ having the melting temperature of at least about 2400°C, selected from the group consisting of C, Mo, and Ta.

205. (Currently amended) The method of claim 200 wherein the first layer is formed by sputter deposition from a target comprising the Ti and the one or more alloying elements having at least one of: ~~(1) a standard electrode potential of less than about 1.0V; (2) a melting temperature of at least about 2400°C; and (3) at least a 8 percent difference in atomic radii relative to titanium.~~